

ABSTRACT OF THE DISCLOSURE

A multilayer interconnection structure includes a first interconnection layer having a copper interconnection pattern and a second interconnection layer having an aluminum interconnection layer and formed on the first interconnection layer via an intervening interlayer insulation film, wherein a tungsten plug is formed in a via-hole formed in the interlayer insulation film so as to connect the first interconnection layer and the second interconnection layer electrically. The via-hole has a depth/diameter ratio of 1.25 or more, and there is formed a conductive nitride film between the outer wall of the tungsten plug and an inner wall of the via-hole such that the entirety of the conductive nitride film is formed of a conductive nitride.